

Dr. R.Srinivasan

SSN College of Engineering

TITLE	CITED BY	YEAR
<b>Power Spectral Density Computation and Dominant Frequencies Identification from the Vibration Sensor Output under Random Vibration Environment</b> R Srinivasan, T Tessy, B Lakshmi Defence Science Journal 70 (6), 692		2020
<b>Reconfigurable silicon nanotube using numerical simulations</b> AN Justeena, R Ambika, P Sadagopan, R Srinivasan JOURNAL OF COMPUTATIONAL ELECTRONICS 19 (3), 966-974		2020
<b>Reconfigurable FET-Based SRAM and its single event upset performance analysis using TCAD simulations</b> AN Justeena, R Srinivasan Microelectronics Journal, 104815	1	2020
<b>Single-event radiation performance analysis of junction and junctionless FET-based low-noise amplifiers</b> P Rajendiran, R Srinivasan Journal of Computational Electronics 18 (4), 1162-1172	1	2019
<b>A vision-based deep on-device intelligent bus stop recognition system</b> GK Gudur, A Ramesh Adjunct Proceedings of the 2019 ACM International Joint Conference on ...		2019
<b>Pattern Analysis on Cymatics-based Images for Pronunciation</b> Y Munoth, NV Kumar, V Vishal, LK Pavithra, R Srinivasan 2019 International Conference on Communication and Signal Processing (ICCSP ...		2019
<b>Eye Blink Detection Using Back Ground Subtraction and Gradient-Based Corner Detection for Preventing CVS</b> TS Sharmila, R Srinivasan, KK Nagarajan, S Athithya Procedia Computer Science 165, 781-789	1	2019
<b>Entropy Analysis on Planar Anamorphic Images</b> SBS Chris, LK Pavithra, R Srinivasan, TS Sharmila Procedia Computer Science 165, 774-780		2019
<b>Heavy ion impact on narrow band cascoded low noise amplifier</b> P Rajendiran, R Srinivasan Microelectronics Reliability 91, 31-37	2	2018
<b>Nanoscale junctionless devices using ringFET structure on bulk silicon substrate</b> SP Scarlet, R Srinivasan, P Sasikala International Journal of Electronics Letters 6 (4), 468-480	1	2018

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<b>Optimization of nanometer bulk junctionless Trigate FET using gate and isolation dielectric engineering</b> SP Scarlet, R Srinivasan Materials Science in Semiconductor Processing 84, 107-114	5	2018
<b>Impact of Doping and Spacer on the Performance of Bulk Planar Junctionless devices</b> SP Scarlet, R Srinivasan 2018 4th International Conference on Electrical Energy Systems (ICEES), 267-273	1	2018
<b>SITUATION AWARE TOPIC ANALYSIS FOR KEYNOTE/SPEAKER EVENTS</b> R Srinivasan, T Kundu, CD Venkatesh, S Saluja		2018
<b>Performance optimisation of junctionless FET in nano regime using segmented channel-A 3D numerical simulation study</b> SP Scarlet, B Prasannanjaneyulu, R Srinivasan Superlattices and Microstructures 111, 1233-1243	1	2017
<b>Sensitivity of Silicon Nanotube Field Effect Transistor to Structural Process Parameters</b> R Ambika, R Srinivasan Journal of Nanoelectronics and Optoelectronics 12 (10), 1098-1104	1	2017
<b>SET and SEU performance of single, double, triple and quadruple-gate junctionlessFETs using numerical simulations</b> N Vinodhkumar, R Srinivasan Microelectronics journal 67, 38-42		2017
<b>Numerical modeling of process parameters on RF metrics in FinFETs, junctionless, and gate-all-around devices</b> B Lakshmi, R Srinivasan International Journal of Numerical Modelling: Electronic Networks, Devices ...	6	2017
<b>Effect of eccentricity on junction and junctionless based silicon nanowire and silicon nanotube FETs</b> SP Scarlet, R Ambika, R Srinivasan Superlattices and Microstructures 107, 178-188	6	2017
<b>SET analysis of silicon nanotube FET</b> GD Jayakumar, R Srinivasan Journal of Computational Electronics 16 (2), 307-315	8	2017
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<b>Performance optimization of RingFET using LDD implantation</b> VM Shobana, R Srinivasan, V Vaithianathan, KK Nagarajan 2017 International Conference on Nextgen Electronic Technologies: Silicon to ...		2017
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<b>Impact of Spacer Engineering on SOI Junctionless FET Performance Using TCAD Simulation</b> P Sasikala, P Scarlet, KK Nagarajan, R Srinivasan Journal of Materials & Metallurgical Engineering 6 (2), 42-52		2016
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